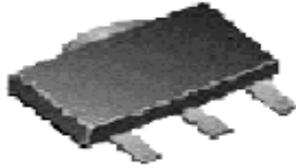


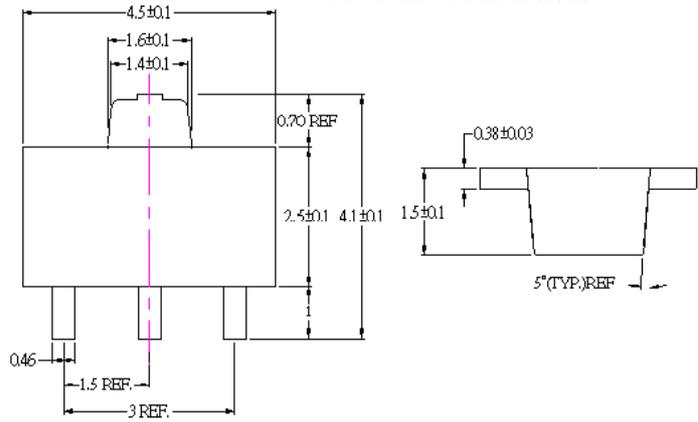
PA10SD

Descriptions



SOT-89

Mechanical Dimensions



Dimension in mm

FEATURES

- · Driven directly with IC and MOS device.
- · Feature proprietary, void-free glass passivated chips.
- · Available in voltage ratings from 200 to 600 volts. (VDRM and VRRM)
- · Sensitive gate trigger current.
- · Designed for high volume, line-powered control application in relay lamp drivers, small motor controls, gate drivers for large thyristors.

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETERS	SYMBOL		V	UNITS
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage (1)	VDRM & VRRM	PA10SD	400	VOLT
RMS On-State Current at Ta=57°C and Conduction Angle of 180°	IT(RMS)	1.0		AMP
Peak Surge (Non-Repetitive) On-State Current, ½ Cycle, at 50Hz or 60Hz	ITSM	8		AMP
Peak Gate-Trigger Current for 3µ sec, Max	IGTM	1.0		AMP
Peak Gate-Power Dissipation at IGT ≤ IGTM	PGM	0.1		WATT
Average Gate-Power Dissipation	PG(AV)	0.01		WATT
Peak gate reverse voltage	VRGM	6		V
Peak Off-State Current, (1) Ta=25°C VDRM & VRRM=Max. Rating Ta=125°C	IDRM & IRRM	10 200		µA MAX
Maximum On-State Voltage. (Peak) At Tc=25°C and IT = Rated Amps	VTM	1.7		VOLT MAX
DC Holding Current, (1)	IHO	10		mA MAX
Critical Rate-Of-Rise of off-State Voltage. (1) Gate Open, Ta=110°C	Critical dv/dt	5		V/µ sec
DC Gate -Trigger Current for Anode Voltage=7VDC, RL=100Ω	IGT	200		µA MAX
DC Gate -Trigger Voltage for Anode Voltage=7VDC, RL=100Ω	VGT	0.8		VOLT MAX
Gate-Controlled Turn-on Time tD+tR IGT=10mA	Tgt	2.2		µ sec
Thermal Resistance, Junction-to-Ambient	Rθ J-A	70		°C/WATT TYP
Storage Temperature range	Tstg	-40 to + 150		°C
Operating Temperature Range, Tj	Tojer	-40 to + 110		°C

(1)RGK=1KΩ

1.0 Amp Silicon Controlled Rectifiers

